

# TMUX154E ESD保護、低容量、電源オフ保護機能搭載の2チャンネル、2:1スイッチ

## 1 特長

- 3V~4.3Vの $V_{CC}$ で動作
- I/Oピンは5.25V許容
- 1.8V互換の制御ロジック
- 電源オフ保護に対応:  $V_{CC} = 0V$ 時、I/OピンはHi-Z
- $R_{ON} = 10\Omega$  (最大値)
- $\Delta R_{ON} = 0.35\Omega$  (標準値)
- $C_{io(ON)} = 7.5pF$  (標準値)
- 低消費電力: 1 $\mu A$  (最大値)
- -3dBの帯域幅 = 900MHz (標準値)
- JESD 78、クラスII準拠で100mA超のラッチアップ性能<sup>(1)</sup>
- ESD性能はJESD 22に準拠しテスト済み
  - 人体モデルで8000V (A114-B、クラスII)
  - 荷電デバイス・モデルで1000V (C101)
- I/OポートからGNDへのESD性能<sup>(2)</sup>
  - 人体モデルで15000V

## 2 アプリケーション

- ポータブル・エレクトロニクス
- プリンタとその他の周辺機器
- 電子POS
- ビルディング・オートメーション
- サーバー

## 3 概要

TMUX154Eは広帯域幅の2:1スイッチで、I/Oが限られているアプリケーションでの高速信号のスイッチングに特化して設計されています。このスイッチは帯域幅が広く(900MHz)、信号が通過するときのエッジやフェーズの歪みが最小限です。このスイッチは双方向で、高速信号の減衰がわずか、または一切発生しません。ビット間のスキューが小さく、チャンネル間のノイズ分離が大きくなるよう設計されています。

TMUX154Eは、すべてのピンにESD保護セルが搭載されており、小型のUQFNパッケージ(1.8mm×1.4mm)またはVSSOPパッケージで供給され、自由通気で-40°C~85°Cの温度範囲で動作が特性付けされています。

### 製品情報<sup>(1)</sup>

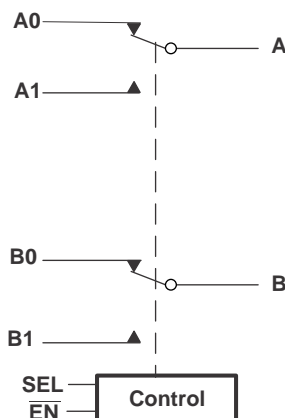
型番	パッケージ	本体サイズ(公称)
TMUX154E	VSSOP (10)	3.00mm×3.00mm
	UQFN (10)	1.80mm×1.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

(1)  $\overline{EN}$ およびSEL入力を除く。

(2) 高電圧HBMは、標準のHBMテスト(A114-B、クラスII)に加えて実行されたもので、GNDを基準としてテストされたI/Oポートにのみ適用されます。

### 機能ブロック図



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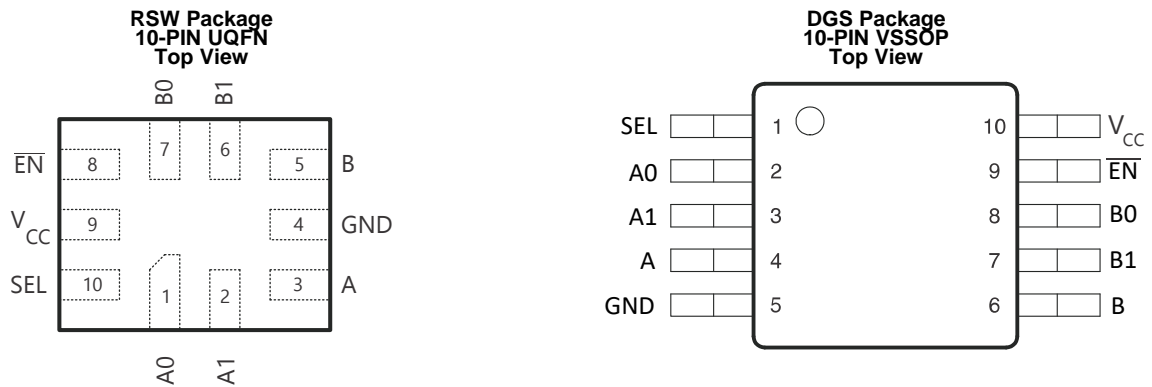
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## 4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

日付	改訂内容	注
2018年2月	*	初版

## 5 Pin Configuration and Functions



### Pin Functions

NAME	PIN		I/O	DESCRIPTION
	UQFN	VSSOP		
A0	1	2	I/O	signal path port 0
B0	7	8	I/O	
A	3	4	I/O	Common signal path
B	5	6	I/O	
A1	2	3	I/O	signal path port 1
B1	6	7	I/O	
EN	8	9	I	EN = 0 Enable EN = 1 Disable
SEL	10	1	I	Select input: SEL = 0 A,B to A0,B0 SEL = 1 A,B to A1,B1
GND	4	5	—	Ground
VCC	9	10	—	Voltage supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (see <sup>(1)</sup> <sup>(2)</sup>)

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage	-0.5	7	V
$V_{SEL}, \overline{V_{EN}}$	Control input voltage	-0.5	7	V
$V_{I/O}$	Signal path I/O voltage	$V_{CC} > 0$	$V_{CC} + 0.3$	V
		$V_{CC} = 0$	5.25	
$I_{IK}$	Control input clamp current	$V_{IN} < 0$	-50	mA
$I_{I/OK}$	I/O port clamp current	$V_{I/O} < 0$	-50	mA
$I_{I/O}$	ON-state switch current		±64	mA
	Continuous current through $V_{CC}$ or GND		±100	mA
$T_{stg}$	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.

### 6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	All pins	±8000
			I/O port to GND	±15000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>		±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

See <sup>(1)</sup>.

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage	3	4.3	V
$V_{IH}$	High-level control input voltage	$V_{CC} = 3\text{ V to }3.6\text{ V}$	1.3	$V_{CC}$
		$V_{CC} = 4.3\text{ V}$	1.7	$V_{CC}$
$V_{IL}$	Low-level control input voltage	$V_{CC} = 3\text{ V to }3.6\text{ V}$	0	0.5
		$V_{CC} = 4.3\text{ V}$	0	0.7
$V_{I/O}$	Data input/output voltage	0	$V_{CC}$	V
$T_A$	Operating ambient temperature	-40	85	°C

- (1) All unused control inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to *Implications of Slow or Floating CMOS Inputs* (SCBA004).

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TMUX154E		UNIT
		DGS (VSSOP)	RSW (UQFN)	
		10 PINS	10 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	203.1	114.5	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	88.7	64.7	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	123.0	21.0	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	21.2	1.9	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	121.6	21.0	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
I <sub>SEL</sub> , I <sub>EN</sub>	Control inputs	V <sub>CC</sub> = 4.3 V, 0 V, V <sub>SEL</sub> , V <sub>EN</sub> = 0 to 4.3 V			±1	μA
I <sub>OZ</sub>	OFF-state leakage current <sup>(3)</sup>	V <sub>CC</sub> = 4.3 V, V <sub>O</sub> = 0 to 3.6 V, V <sub>I</sub> = 0, Switch OFF			±1	μA
I <sub>OFF</sub>	Powered off leakage current	V <sub>CC</sub> = 0 V, V <sub>An,Bn</sub> = 0 V, V <sub>A,B</sub> = 0 V to 4.3 V, V <sub>SEL</sub> , V <sub>EN</sub> = V <sub>CC</sub> or GND			±2	μA
I <sub>CC</sub>	Supply current	V <sub>CC</sub> = 4.3 V, I <sub>I/O</sub> = 0, Switch ON or OFF			1	μA
ΔI <sub>CC</sub> <sup>(4)</sup>	Difference of supply current due to control input voltage not V <sub>CC</sub> or GND	V <sub>CC</sub> = 4.3 V, V <sub>SEL</sub> , V <sub>EN</sub> = 2.6 V			10	μA
C <sub>SEL</sub> , C <sub>EN</sub>	Control inputs digital input capacitance	V <sub>CC</sub> = 0 V, V <sub>SEL</sub> , V <sub>EN</sub> = V <sub>CC</sub> or GND		1		pF
C <sub>I/O(OFF)</sub>	OFF-state input capacitance	V <sub>CC</sub> = 3.3 V, V <sub>I/O</sub> = 3.3 V or 0, Switch OFF		2		pF
C <sub>I/O(ON)</sub>	ON-state input capacitance	V <sub>CC</sub> = 3.3 V, V <sub>I/O</sub> = 3.3 V or 0, Switch ON		7.5		pF
R <sub>ON</sub>	ON-state resistance <sup>(5)</sup>	V <sub>CC</sub> = 3 V, V <sub>I</sub> = 0.4, I <sub>O</sub> = –8 mA		6	10	Ω
ΔR <sub>ON</sub>	ON-state resistance match between channels	V <sub>CC</sub> = 3 V, V <sub>I</sub> = 0.4, I <sub>O</sub> = –8 mA		0.35		Ω
r <sub>on(flat)</sub>	ON-state resistance flatness	V <sub>CC</sub> = 3 V, V <sub>I</sub> = 0 V or 1 V, I <sub>O</sub> = –8 mA		2		Ω

(1) V<sub>I</sub>, V<sub>O</sub>, I<sub>I</sub>, and I<sub>O</sub> refer to data I/O pins A, B, An, and Bn.

(2) All typical values are at V<sub>CC</sub> = 3.3 V (unless otherwise noted), T<sub>A</sub> = 25°C.

(3) For I/O ports, the parameter I<sub>OZ</sub> includes the input leakage current.

(4) This is the increase in supply current for each digital control input that is supplied with a voltage other than V<sub>CC</sub> or GND.

(5) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

## 6.6 Dynamic Electrical Characteristics

 over operating range,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V} \pm 10\%$ ,  $\text{GND} = 0\text{ V}$ 

PARAMETER		TEST CONDITIONS	TYP <sup>(1)</sup>	UNIT
X <sub>TALK</sub>	Crosstalk	$R_L = 50\ \Omega$ , $f = 1\ \text{MHz}$ , See <a href="#">6</a>	-97	dB
O <sub>ISO</sub>	OFF isolation	$R_L = 50\ \Omega$ , $f = 1\ \text{MHz}$ , See <a href="#">5</a>	-85	dB
BW	Bandwidth (-3 dB)	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">7</a>	900	MHz

 (1) For Max or Min conditions, use the appropriate value specified under [Electrical Characteristics](#) for the applicable device type.

## 6.7 Switching Characteristics

 over operating range,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V} \pm 10\%$ ,  $\text{GND} = 0\text{ V}$ 

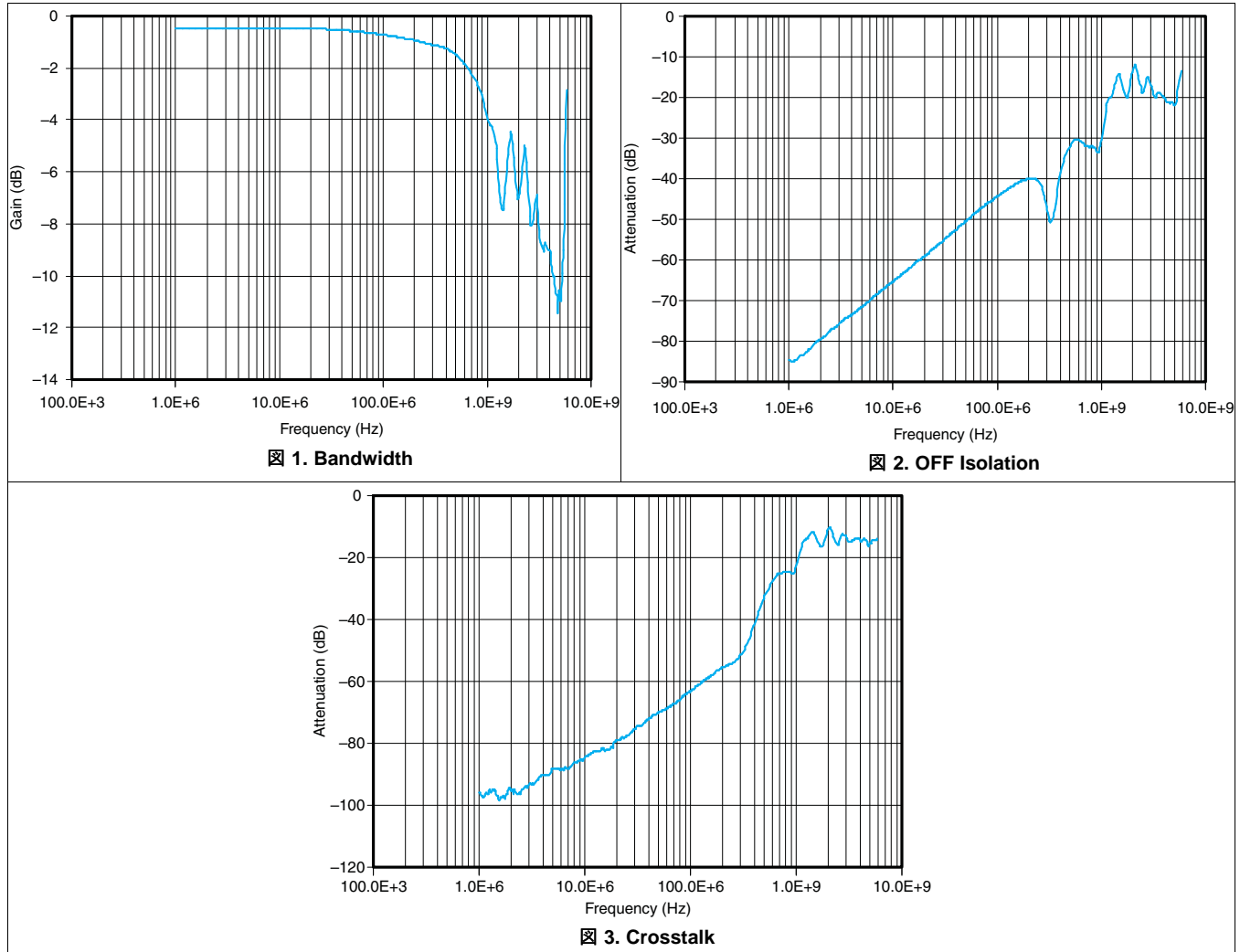
PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
t <sub>pd</sub>	Propagation delay <sup>(2)</sup> <sup>(3)</sup>	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">8</a>		0.25		ns
t <sub>ON</sub>	Line enable time, SEL to A, B, An, or Bn	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">4</a>			30	ns
t <sub>OFF</sub>	Line disable time, SEL to A, B, An, or Bn	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">4</a>			25	ns
t <sub>ON</sub>	Line enable time, $\overline{\text{OE}}$ to A, B, An, or Bn	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">4</a>			30	ns
t <sub>OFF</sub>	Line disable time, $\overline{\text{OE}}$ to A, B, An, or Bn	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">4</a>			25	ns
t <sub>SK(O)</sub>	Output skew between center port to any other port <sup>(2)</sup>	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">9</a>			50	ps
t <sub>SK(P)</sub>	Skew between opposite transitions of the same output (t <sub>PHL</sub> - t <sub>PLH</sub> ) <sup>(2)</sup>	$R_L = 50\ \Omega$ , $C_L = 5\ \text{pF}$ , See <a href="#">9</a>			20	ps

 (1) For Max or Min conditions, use the appropriate value specified under [Electrical Characteristics](#) for the applicable device type.

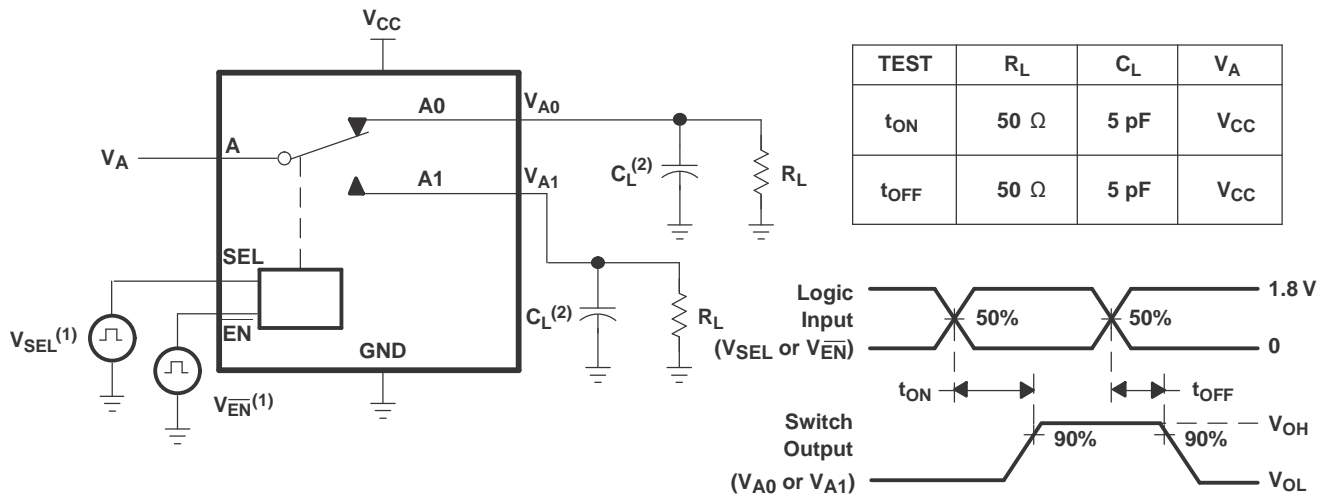
(2) Specified by design

(3) The bus switch contributes no propagational delay other than the RC delay of the on resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25 ns for 10-pF load. Since this time constant is much smaller than the rise/fall times of typical driving signals, it adds very little propagational delay to the system. Propagational delay of the bus switch, when used in a system, is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.

### 6.8 Typical Characteristics



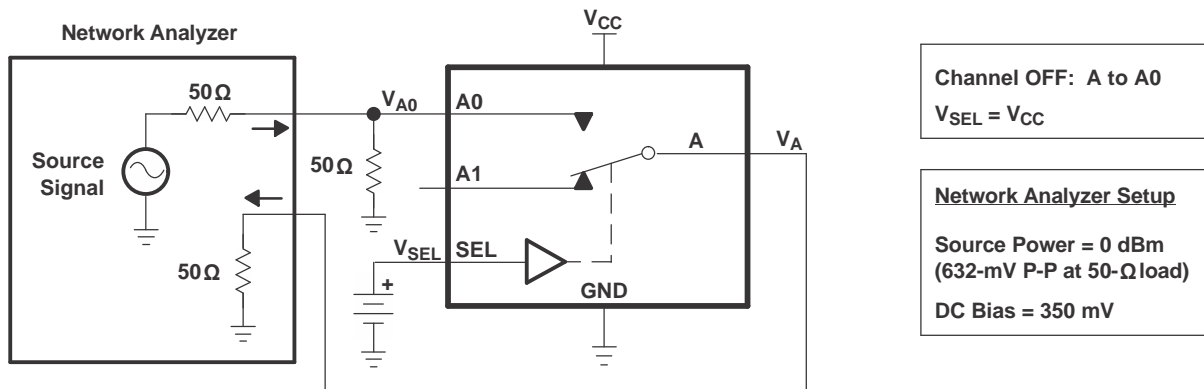
## 7 Parameter Measurement Information



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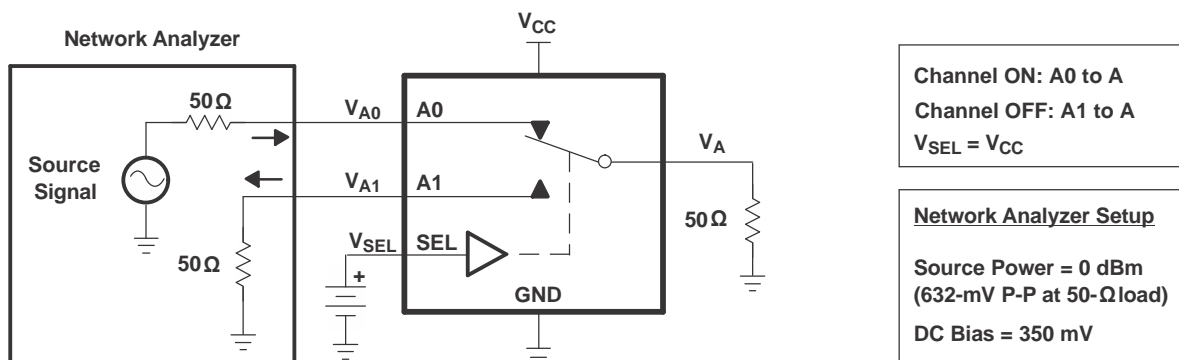
- (1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>O</sub> = 50 Ω, t<sub>r</sub> < 5 ns, t<sub>f</sub> < 5 ns.
- (2) C<sub>L</sub> includes probe and jig capacitance.

☒ 4. Turn-On (t<sub>ON</sub>) and Turn-Off Time (t<sub>OFF</sub>)



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☒ 5. OFF Isolation (O<sub>ISO</sub>)

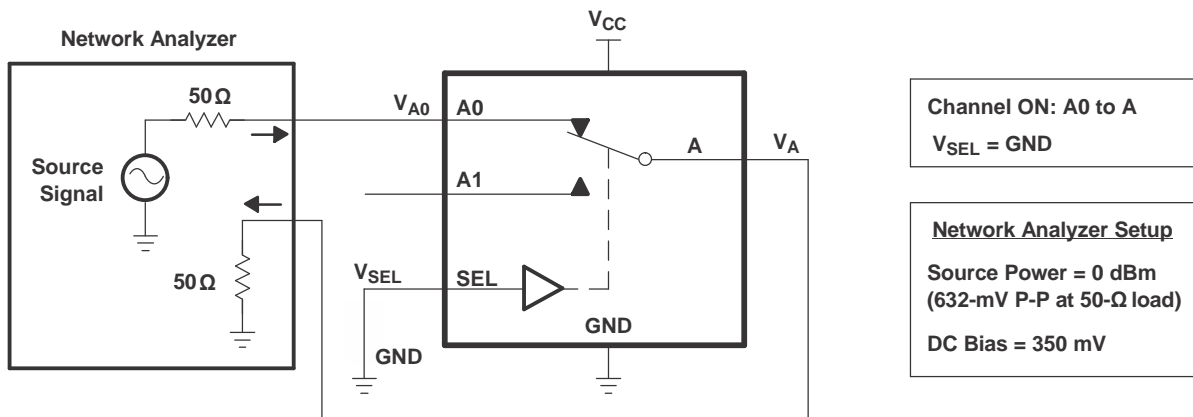


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☒ 6. Crosstalk (X<sub>TALK</sub>)

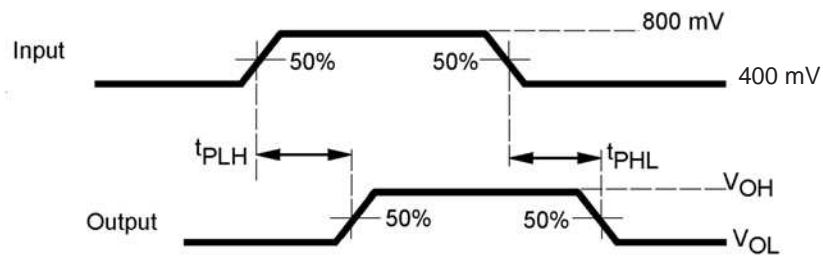


**Parameter Measurement Information (continued)**



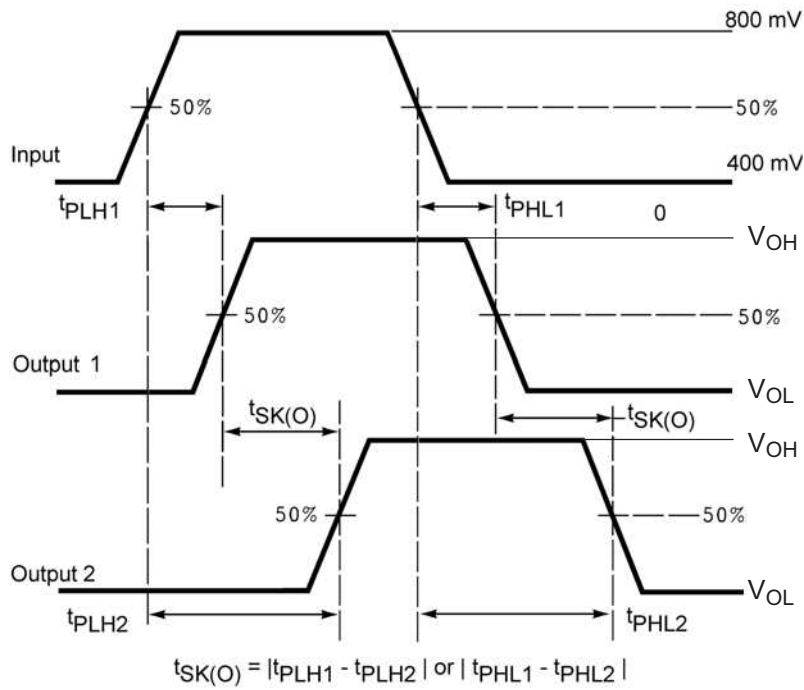
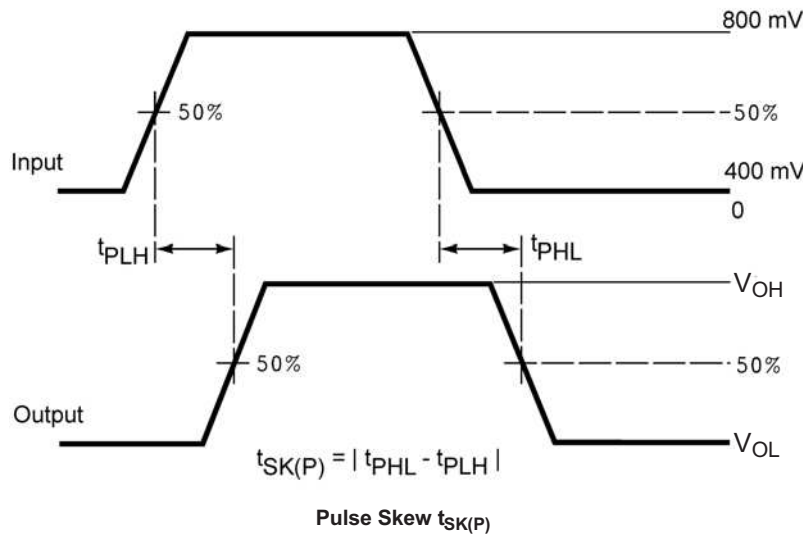
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**图 7. Bandwidth (BW)**



**图 8. Propagation Delay**

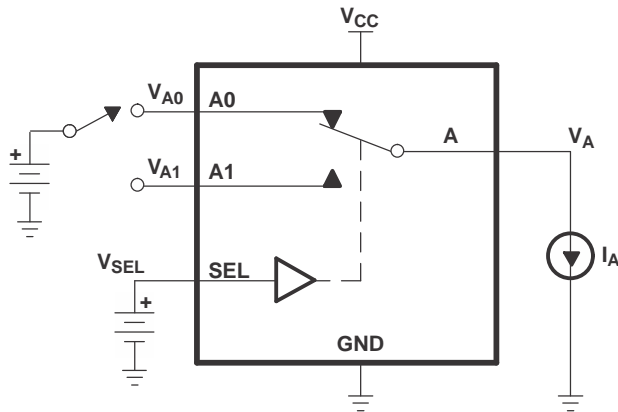
**Parameter Measurement Information (continued)**



**Output Skew  $t_{SK(P)}$**

**☒ 9. Skew Test**

Parameter Measurement Information (continued)



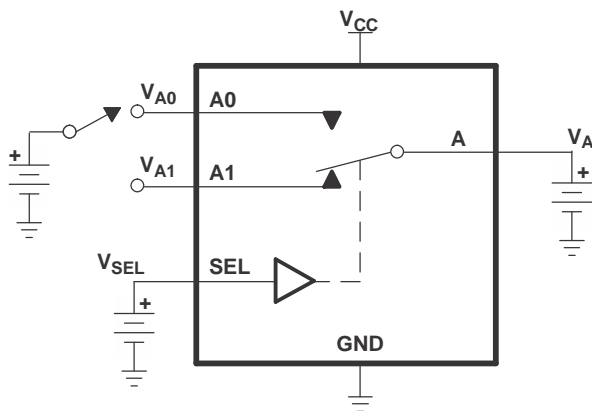
Channel ON  

$$r_{on} = \frac{V_A - V_{A0}}{I_{IN}}$$

$$V_{SEL} = GND$$

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10. ON-State Resistance ( $R_{ON}$ )

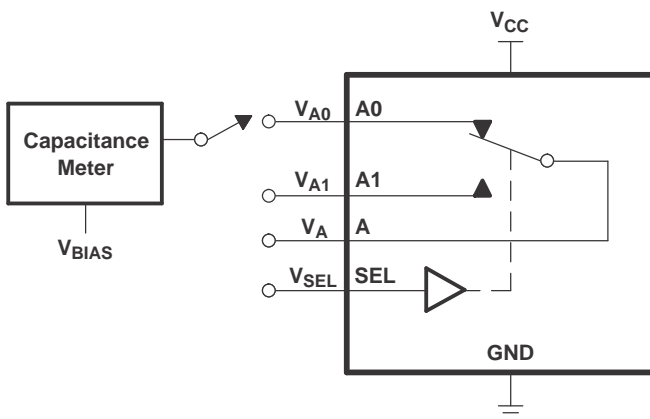


OFF-State Leakage Current  
 Channel OFF  

$$V_{SEL} = V_{IH} \text{ or } V_{CC}$$

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11. OFF-State Leakage Current



$$V_{BIAS} = V_{CC} \text{ or } GND$$

$$V_{SEL} = V_{CC} \text{ or } GND$$
 Capacitance is measured at A0, A1, A and SEL inputs during on and off conditions

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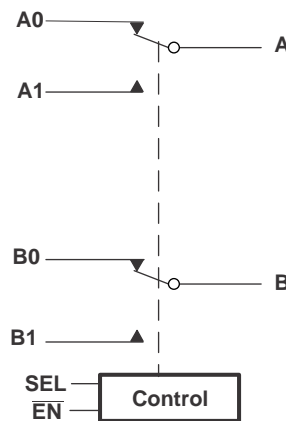
12. Capacitance

## 8 Detailed Description

### 8.1 Overview

The TMUX154E is a high-bandwidth switch specially designed for the switching and isolating of high-speed signals in systems with limited I/Os. The wide bandwidth (900 MHz) of this switch allows signals to pass with minimum edge and phase distortion. The device multiplexes differential or single ended signals from a single device to one of two corresponding outputs or from two different different devices to one single output. The switch is bidirectional and offers little or no attenuation of the high-speed signals. It is designed for low bit-to-bit skew and high channel-to-channel noise isolation.

### 8.2 Functional Block Diagram



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### 8.3 Feature Description

The TMUX154E has an enable pin  $\overline{EN}$  that can place the signal paths in high impedance. This allows the user to isolate the signal path when it is not in use and consume less current.

### 8.4 Device Functional Modes

The device functional modes are shown in [表 1](#).

**表 1. Truth Table**

SEL	$\overline{EN}$	FUNCTION
X	H	Disconnect
L	L	A = A0 B = B0
H	L	A = A1 B = B1

## 9 Application and Implementation

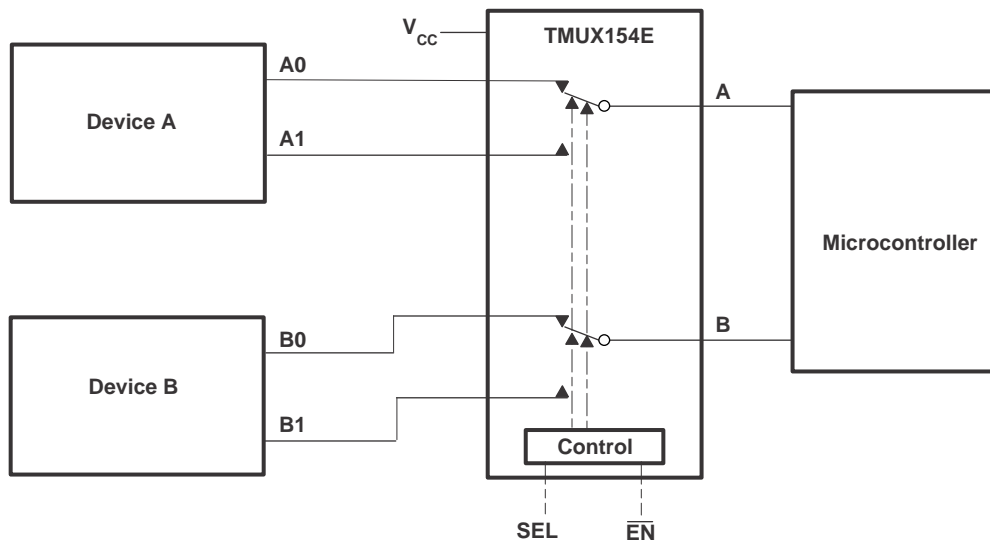
### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

There are many applications in which processors and microcontrollers have a limited number of I/Os. The TMUX154E solution can effectively expand the limited number of I/Os by switching between multiple signal paths in order to interface them to a single processor or microcontroller. TMUX154E can also be used to connect a single microcontroller to two signal paths.

### 9.2 Typical Application



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图 13. Application Diagram

#### 9.2.1 Design Requirements

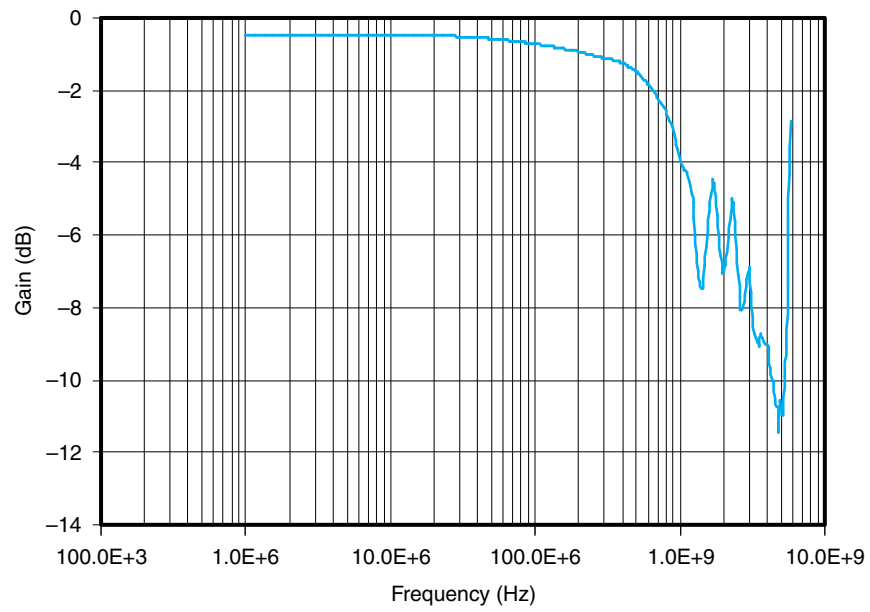
TI recommends that the digital control pins SEL and  $\overline{EN}$  be pulled up to V<sub>CC</sub> or down to GND to avoid undesired switch positions that could result from the floating pin.

#### 9.2.2 Detailed Design Procedure

The TMUX154E can be properly operated without any external components. However, it is recommended that unused pins be connected to ground through a 50-Ω resistor to prevent signal reflections back into the device.

**Typical Application (continued)**

**9.2.3 Application Curves**



**14. Bandwidth**

## 10 Power Supply Recommendations

TI recommends placing a bypass capacitor as close as possible to the supply pin  $V_{CC}$  to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

## 11 Layout

### 11.1 Layout Guidelines

Place supply bypass capacitors as close to  $V_{CC}$  pin as possible and avoid placing the bypass caps near the signal traces.

The high-speed traces should always be of equal length and must be no more than 4 inches; otherwise, the eye diagram performance may be degraded.

Route the high-speed signals using a minimum of vias and corners which will reduce signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the transmission line of the signal and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.

When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.

Do not route signal traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices, or IC's that use or duplicate clock signals.

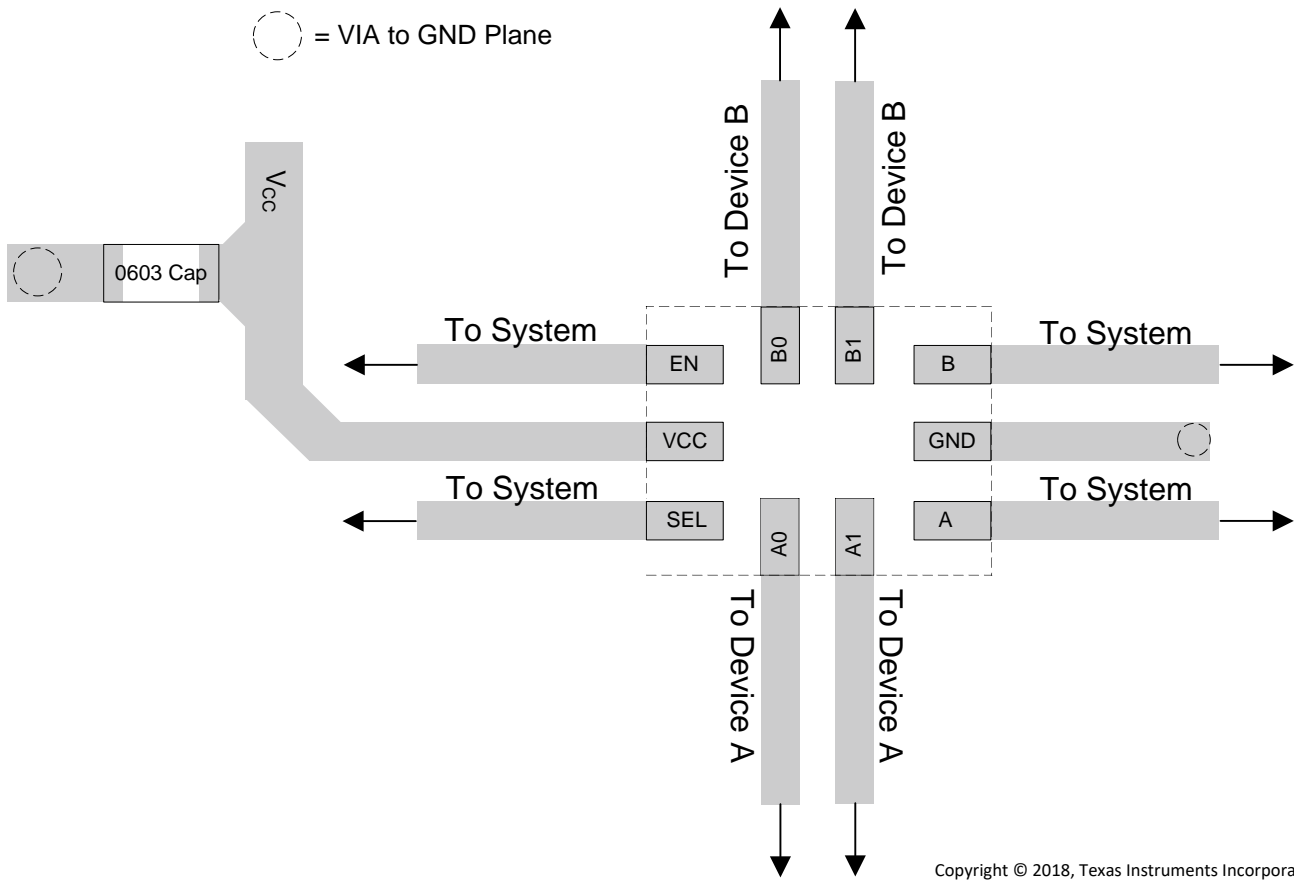
Avoid stubs on the high-speed signals because they cause signal reflections.

Route all high-speed signal traces over continuous planes ( $V_{CC}$  or  $GND$ ), with no interruptions.

Avoid crossing over anti-etch, commonly found with plane splits.

For high frequency systems, a printed circuit board with at least four layers is recommended: two signal layers separated by a ground layer and a power layer. The majority of signal traces should run on a single layer, preferably Signal 1. Immediately next to this layer should be the  $GND$  plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies. For more information on layout guidelines, see *High Speed Layout Guidelines (SCAA082)*

**11.2 Layout Example**



**15. Layout Recommendation**



## 12 デバイスおよびドキュメントのサポート

### 12.1 ドキュメントのサポート

#### 12.1.1 関連資料

関連資料については、以下を参照してください。

- 『低速またはフローティングCMOS入力の影響』、[SCBA004](#)
- 『高速レイアウトのガイドライン』、[SCAA082](#)

### 12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](http://ti.com)のデバイス製品フォルダを開いてください。右上の隅にある「通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

### 12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

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**設計サポート** *TIの設計サポート* 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

### 12.4 商標

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

### 12.5 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

### 12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

### 13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TMUX154EDGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAUAG   SN	Level-1-260C-UNLIM	-40 to 85	1A6	<a href="#">Samples</a>
TMUX154ERSWR	ACTIVE	UQFN	RSW	10	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BXV	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

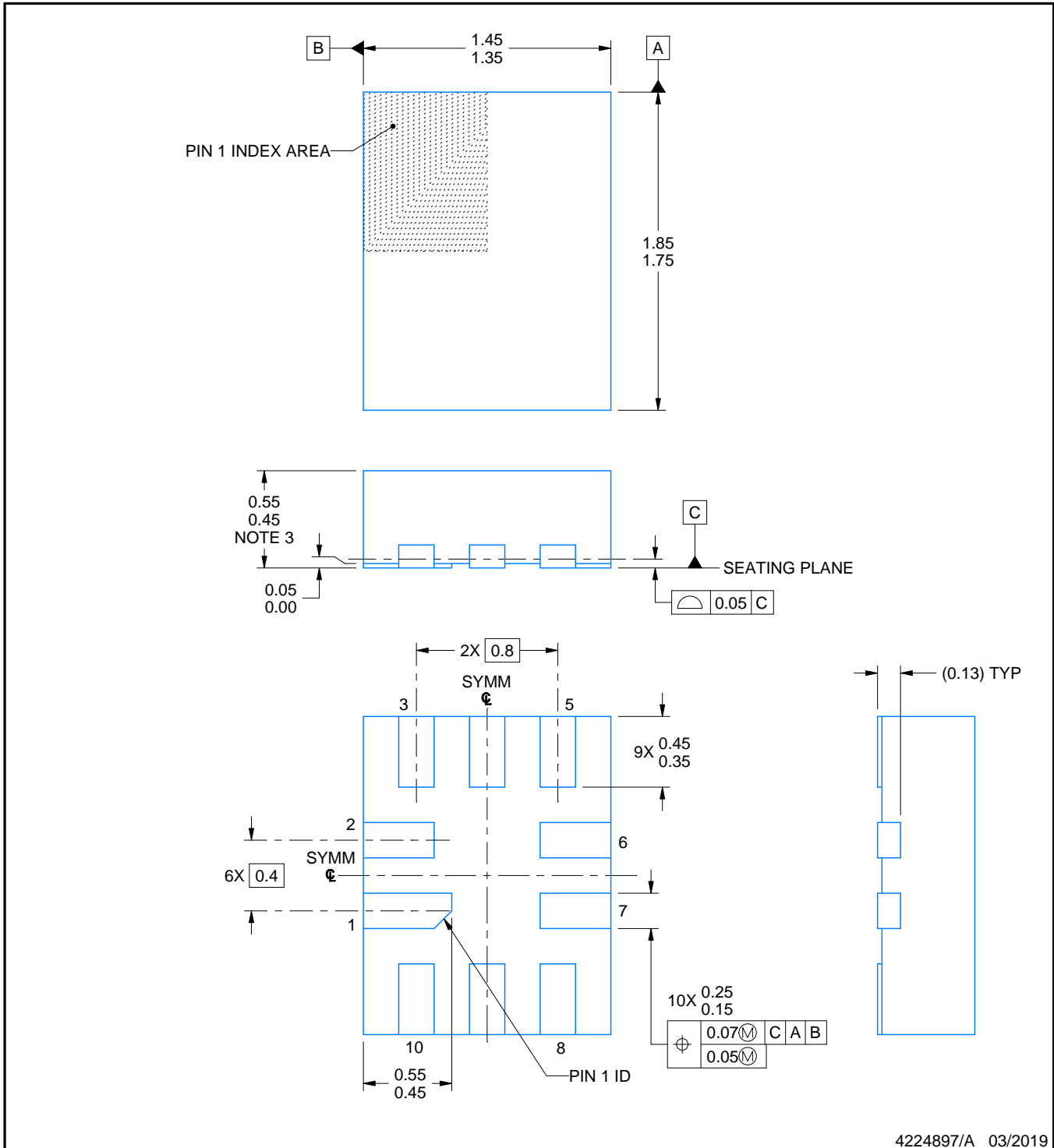
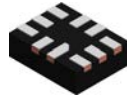
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX154EDGSR	VSSOP	DGS	10	2500	330.0	12.4	5.25	3.35	1.25	8.0	12.0	Q1
TMUX154ERSWR	UQFN	RSW	10	3000	180.0	8.4	1.7	2.1	0.7	4.0	8.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX154EDGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0
TMUX154ERSWR	UQFN	RSW	10	3000	210.0	185.0	35.0



4224897/A 03/2019

NOTES:

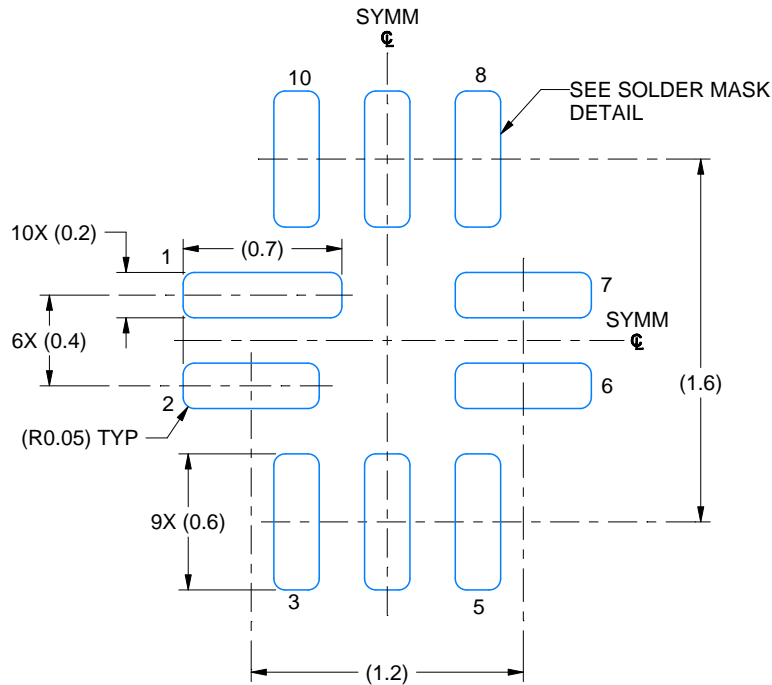
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package complies to JEDEC MO-288 variation UDEE, except minimum package height.

# EXAMPLE BOARD LAYOUT

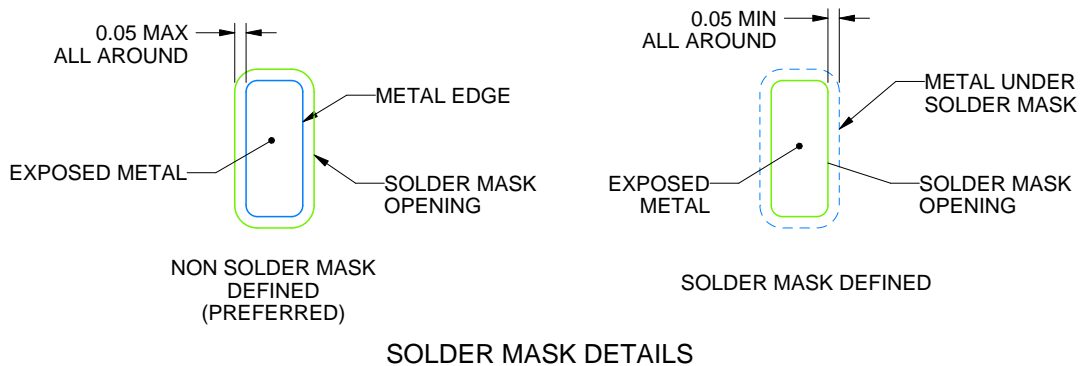
RSW0010A

UQFN - 0.55 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 30X



SOLDER MASK DETAILS

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NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

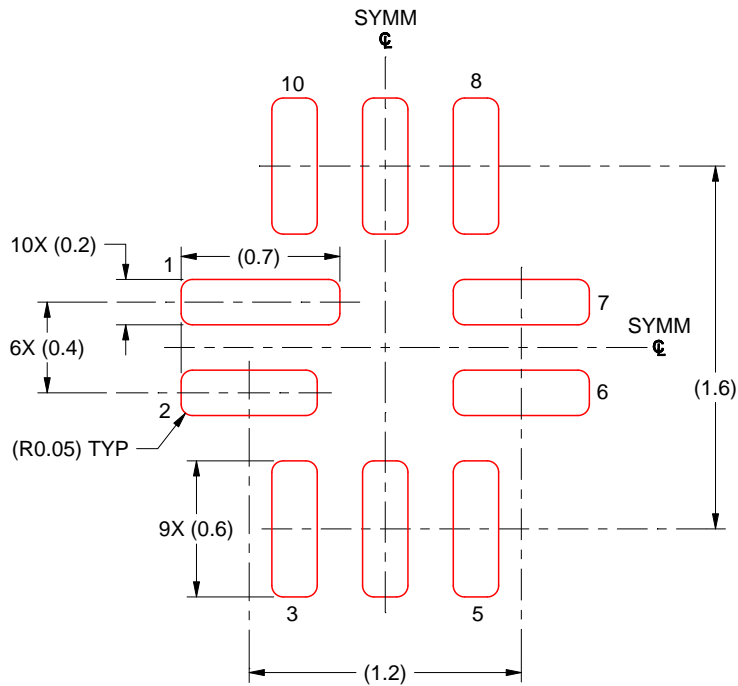


# EXAMPLE STENCIL DESIGN

RSW0010A

UQFN - 0.55 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.125 MM THICK STENCIL  
SCALE: 30X

4224897/A 03/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

# DGS0010A



# PACKAGE OUTLINE

## VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4221984/A 05/2015

### NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187, variation BA.

# EXAMPLE BOARD LAYOUT

DGS0010A

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
SCALE:10X



SOLDER MASK DETAILS  
NOT TO SCALE

4221984/A 05/2015

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DGS0010A

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:10X

4221984/A 05/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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